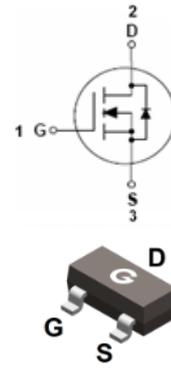


### Features

- Advanced trench technology
- Low input capacitance
- High  $V_{DSS}$  rating for power application
- Low input / output leakage
- RoHS compliant with Halogen-free

HF



SOT-23

### Mechanical Data

- Case: SOT-23
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matted-Tin plated; Solderable Per MIL-STD-202, Method 208

### Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BSS127	SOT-23	3000 pcs / Tape & Reel	K29

### Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	600	V
Gate-to-Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Drain Current ( $T_A = 25^\circ\text{C}$ ) <sup>*1</sup>	$I_D$	60	mA
Continuous Drain Current ( $T_A = 70^\circ\text{C}$ ) <sup>*1</sup>		48	mA
Pulsed Drain Current ( $t_p = 10\mu\text{s}$ , $T_A = 25^\circ\text{C}$ )	$I_{DM}$	240	mA
Power Dissipation ( $T_A = 25^\circ\text{C}$ ) <sup>*1</sup>	$P_D$	1.25	W
Power Dissipation ( $T_A = 25^\circ\text{C}$ ) <sup>*2</sup>		0.61	W
Operating Junction Temperature Range	$T_J$	-55 ~ +150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Air <sup>*1</sup>	$R_{\theta JA}$	-	70	100	$^\circ\text{C}/\text{W}$
Thermal Resistance Junction-to-Air <sup>*2</sup>		-	-	204	$^\circ\text{C}/\text{W}$

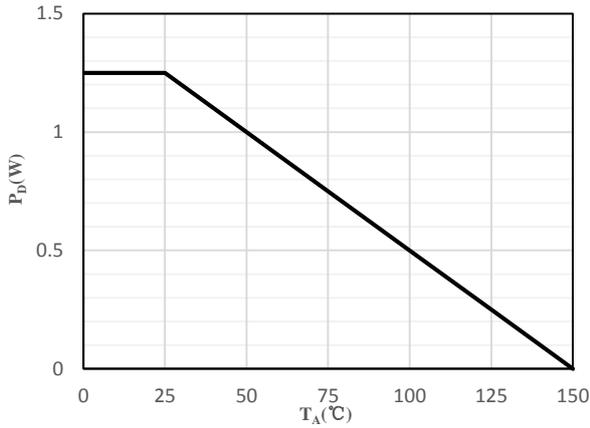
### Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
$V_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	600	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	-	-	0.1	$\mu A$
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$R_{DS(ON)}$	Drain-Source On-resistance <sup>*3</sup>	$V_{GS} = 10V, I_D = 16mA$	-	30	160	$\Omega$
		$V_{GS} = 5V, I_D = 16mA$	-	31	190	$\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3	4	V
$R_G$	Gate Resistance	$V_{GS} = 0V, f = 1MHz$	-	120	-	$\Omega$
<b>Dynamic Characteristics</b>						
$C_{ISS}$	Input Capacitance	$V_{GS} = 0V$	-	36	-	pF
$C_{OSS}$	Output Capacitance	$V_{DS} = 25V$	-	6	-	
$C_{RSS}$	Reverse Transfer Capacitance	$f = 1.0MHz$	-	0.8	-	
<b>Switching Characteristics</b>						
$t_{d(ON)}$	Turn-on Delay Time <sup>*4</sup>	$V_{DD} = 100V$ $V_{GS} = 10V$ $R_G = 25\Omega$ $I_D = 0.2A$	-	30	-	ns
$t_r$	Turn-on Rise Time <sup>*4</sup>		-	10	-	
$t_{d(OFF)}$	Turn-Off Delay Time <sup>*4</sup>		-	53	-	
$t_f$	Turn-Off Fall Time <sup>*4</sup>		-	18	-	
$Q_G$	Total Gate-Charge	$V_{DD} = 300V$	-	0.65	-	nC
$Q_{GS}$	Gate to Source Charge	$I_D = 0.01A$	-	0.07	-	
$Q_{GD}$	Gate to Drain (Miller) Charge	$V_{GS} = 10V$	-	0.31	-	
<b>Source-Drain Diode Characteristics</b>						
$V_{SD}$	Diode Forward Voltage <sup>*3</sup>	$I_{SD} = 16mA, V_{GS} = 0V$	-	0.7	1.5	V
$t_{rr}$	Reverse Recovery Time	$I_F = 16mA, V_{GS} = 0V$	-	160	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di/dt = 100A/\mu s$	-	13.2	-	nC

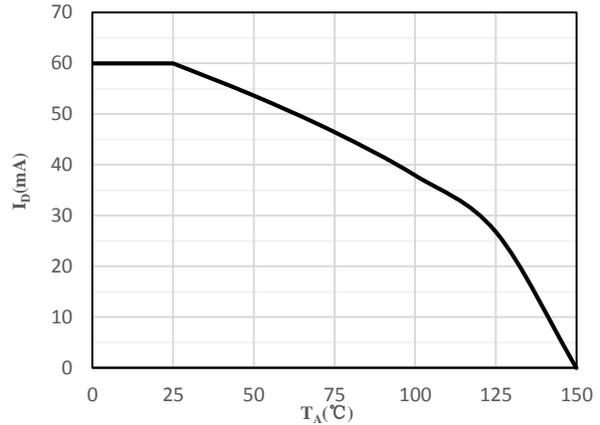
Notes:

1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper
2. The data tested by surface mounted on a minimum recommended FR-4 board
3. The data tested by pulsed, pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
4. Guaranteed by design, not subject to production

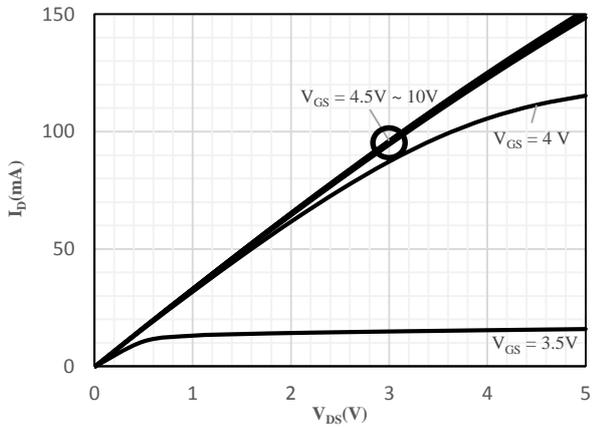
**Ratings and Characteristics Curves** (@  $T_A = 25^\circ\text{C}$  unless otherwise specified)



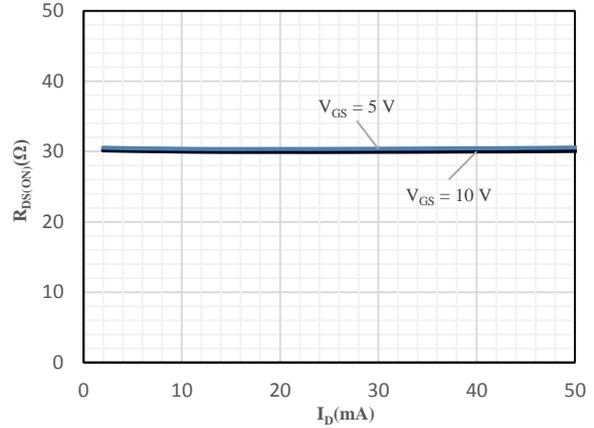
**Fig 1 Power Dissipation**



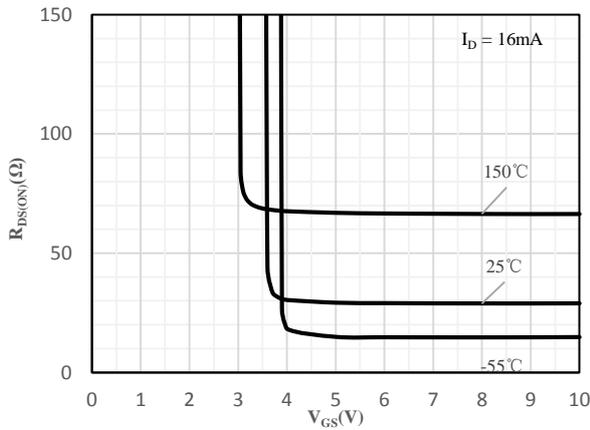
**Fig 2 Drain Current**



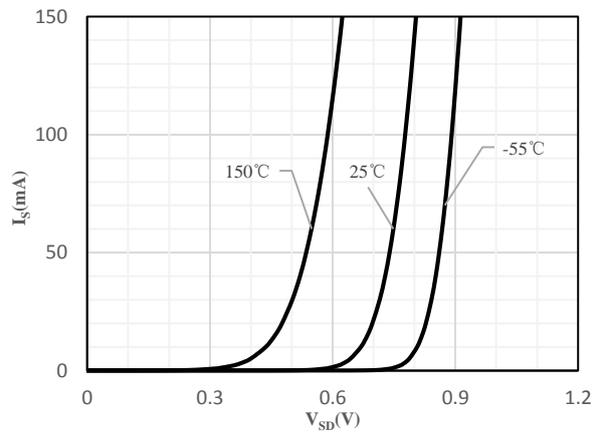
**Fig 3 Typical Output Characteristics**



**Fig 4 On-Resistance vs. Drain Current and Gate Voltage**



**Fig 5 On-Resistance vs. Gate-Source Voltage**



**Fig 6 Body-Diode Characteristics**

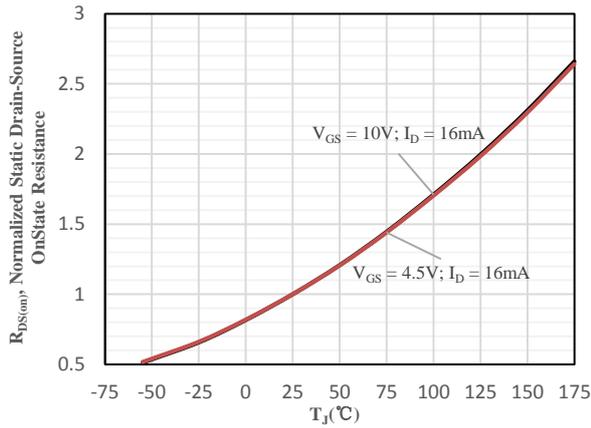


Fig 7 Normalized On-Resistance vs. Junction Temperature

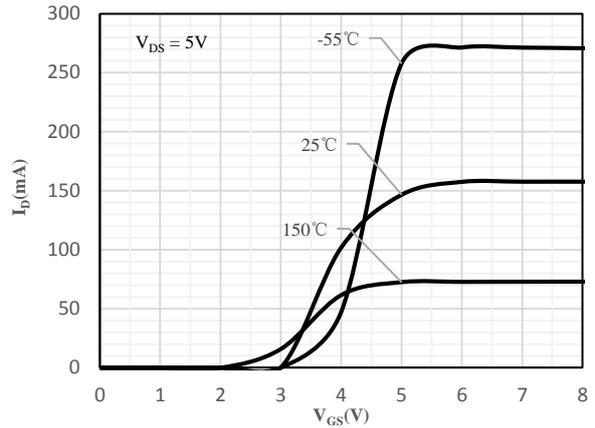


Fig 8 Transfer Characteristics

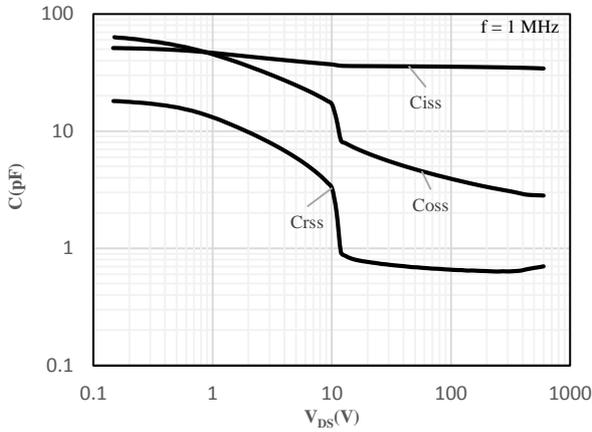


Fig 9 Capacitance Characteristics

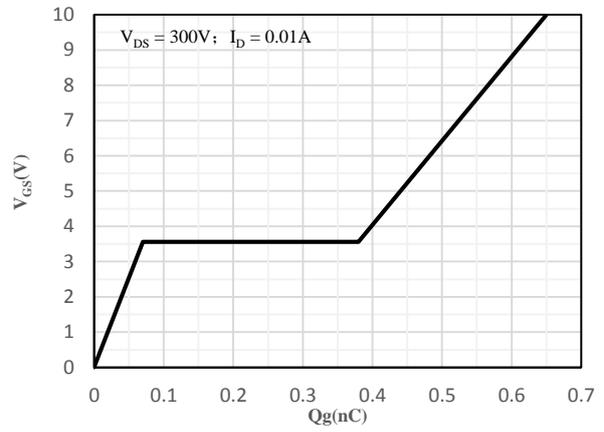


Fig 10 Gate-Charge Characteristics

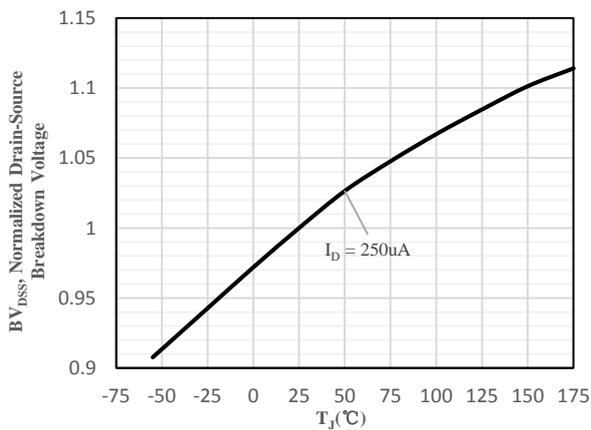


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

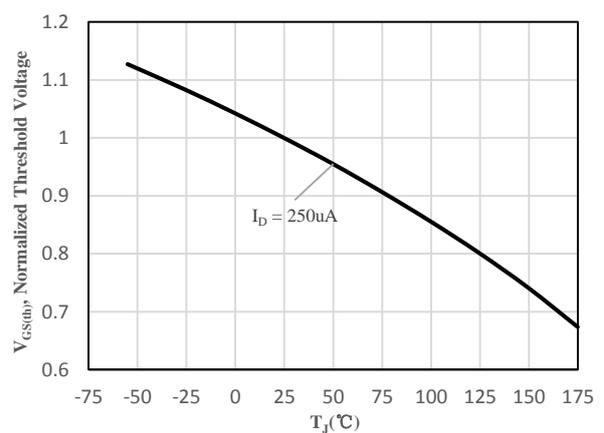
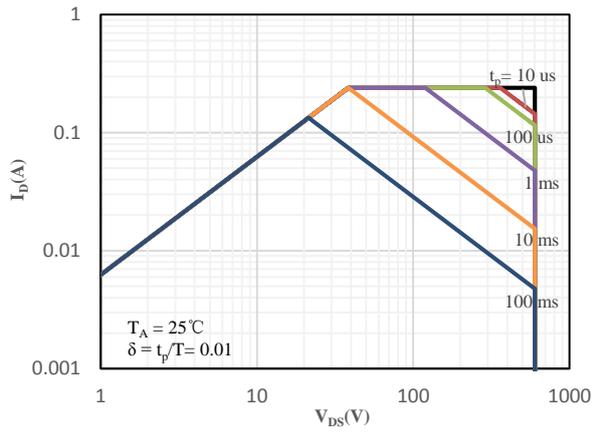
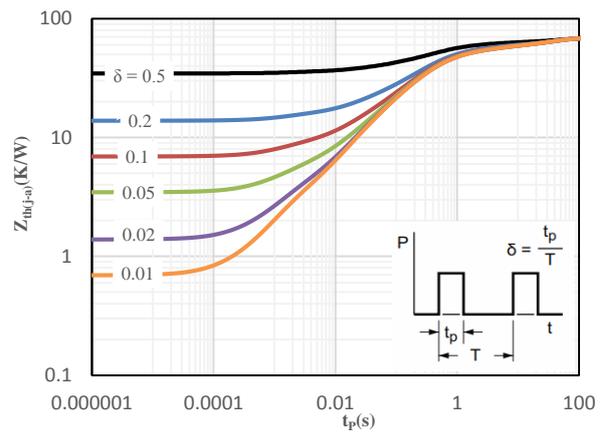


Fig 12 Normalized  $V_{GS(th)}$  vs. Junction Temperature

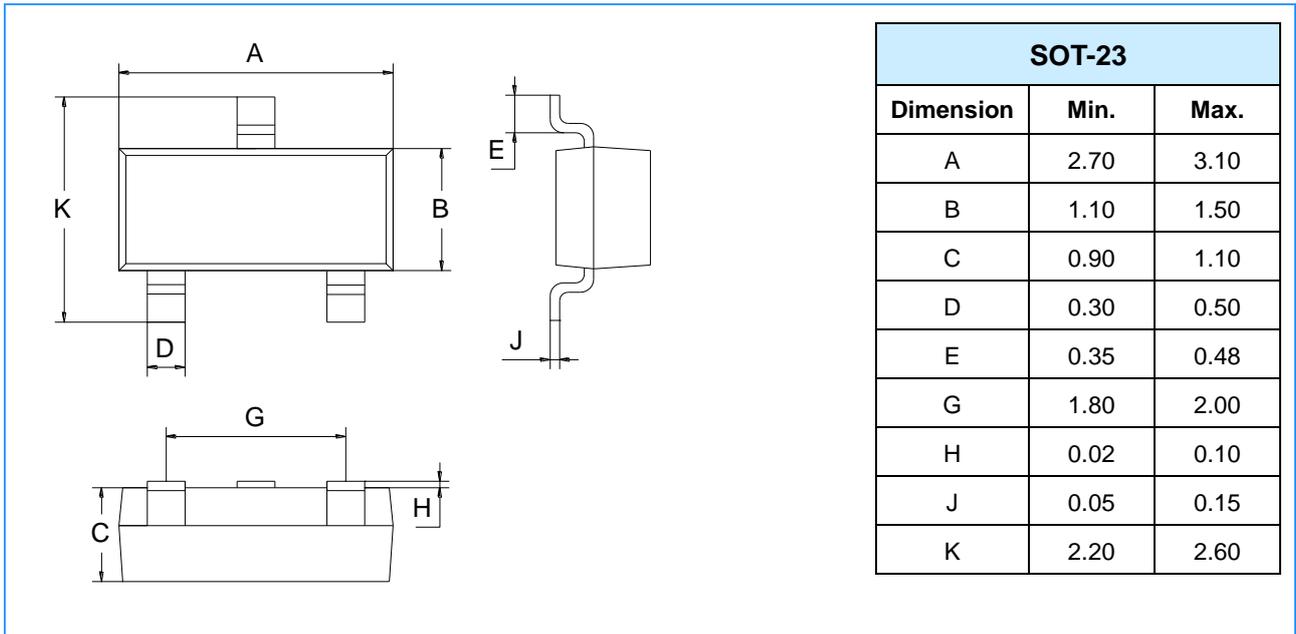


**Fig 13 Safe Operating Area**



**Fig 14 Maximum transient thermal impedance**

**Package Outline Dimensions** (Unit: mm)



**Mounting Pad Layout** (Unit: mm)

